L Number	Hits	Search Text	DB	Time stamp
-	42	"5302966"	USPAT	2004/08/09 07:44
-	12	"5587329"	USPAT	2004/08/09 08:57
-	34744	high$1voltage low$1voltage	USPAT; US-PGPUB	2004/08/09 10:07
-	535	(high$1voltage low$1voltage) and (silicon$1on$1insulat$5)	USPAT; US-PGPUB	2004/08/09 08:58
-	958	(high$1voltage low$1voltage) and (soi silicon$1on$1insulat$5)	USPAT; US-PGPUB	2004/08/09 08:59
-	305	((high$1voltage low$1voltage) and (soi silicon$1on$1insulat$5)) and (thicker with (device near region) (semiconductor near layer) (low$1voltage near region))	USPAT; US-PGPUB	2004/08/09 09:05
-	3	(high$1voltage near region) and (low$1voltage near region) and soi	USPAT; US-PGPUB	2004/08/09 10:11
-	2	(high$1voltage near device) and (low$1voltage near device) and soi	USPAT; US-PGPUB	2004/08/09 10:32
-	279	257/500.ccls.	USPAT; US-PGPUB	2004/08/09 11:37
-	559	438/479.ccls. not (257/500.ccls.)	USPAT; US-PGPUB	2004/08/09 12:47
-	80	438/295.ccls. not (438/479.ccls. 257/500.ccls.)	USPAT; US-PGPUB	2004/08/09 12:59
-	53	438/219.ccls. not (438/295.ccls. 438/479.ccls. 257/500.ccls.)	USPAT; US-PGPUB	2004/08/09 13:07
-	140	438/224.ccls. not (438/219.ccls. 438/295.ccls. 438/479.ccls. 257/500.ccls.)	USPAT; US-PGPUB	2004/08/09 13:22
-	291	438/404.ccls. not (438/224.ccls. 438/219.ccls. 438/295.ccls. 438/479.ccls. 257/500.ccls.)	USPAT; US-PGPUB	2004/08/09 14:03
-	123	438/412.ccls. not (438/404.ccls. 438/224.ccls. 438/219.ccls. 438/295.ccls. 438/479.ccls. 257/500.ccls.)	USPAT; US-PGPUB	2004/08/10 18:52
-	1560	(silicon$1on$1insulator soi) and (nitride with oxide with remov$5)	USPAT; US-PGPUB	2004/08/10 13:06
-	216	((silicon$1on$1insulator soi) and (nitride with oxide with remov$5)) and (high adj voltage$1)	USPAT; US-PGPUB	2004/08/10 15:26
-	1	"10367265"	JPO; DERWENT	2004/08/10 15:12
-	1791	(silicon$1on$1insulator soi) and ((nitride with oxide) same thin$5)	USPAT; US-PGPUB	2004/08/10 15:37
-	992	((silicon$1on$1insulator soi) and ((nitride with oxide) same thin$5)) and ((nitride with oxide) with thin$5)	USPAT; US-PGPUB	2004/08/10 15:34
-	3022	(silicon$1on$1insulator soi) and (thin$5 with ((semiconductor near layer) (silicon near layer) (high$1voltage near (region area)) (low$1voltage near (region area))))	USPAT; US-PGPUB	2004/08/10 15:42
-	1486	((silicon$1on$1insulator soi) and (thin$5 with ((semiconductor near layer) (silicon near layer) (high$1voltage near (region area)) (low$1voltage near (region area))))) and (((remov$5 etch$5) oxide) with thin$5 with ((semiconductor near layer) (silicon near layer) (high$1voltage near (region area)) (low$1voltage near (region area))))	USPAT; US-PGPUB	2004/08/10 15:45
-	2498	(438/275.ccls. 257/347.ccls.) not (438/412.ccls. 438/404.ccls. 438/224.ccls. 438/219.ccls. 438/295.ccls. 438/479.ccls. 257/500.ccls.)	USPAT; US-PGPUB	2004/08/10 19:00
-	253	((438/275.ccls. 257/347.ccls.) not (438/412.ccls. 438/404.ccls. 438/224.ccls. 438/219.ccls. 438/295.ccls. 438/479.ccls. 257/500.ccls.)) and (high adj voltage) and (low adj voltage)	USPAT; US-PGPUB	2004/08/10 19:01
-	47	(((438/275.ccls. 257/347.ccls.) not (438/412.ccls. 438/404.ccls. 438/224.ccls. 438/219.ccls. 438/295.ccls. 438/479.ccls. 257/500.ccls.)) and (high adj voltage) and (low adj voltage)) and (region near (thick$5 thin$7))	USPAT; US-PGPUB	2004/08/10 19:01

-	1	"20040121547"	DERWENT	2004/08/10 19:11
-	4	(U11-C18A3 and U12-D02A3 and U12-D02A4 and U12-Q).epi.	DERWENT	2004/08/10 19:11
-	1926	(L04-C07 and L04-C12).cpi.	DERWENT	2004/08/10 19:12
-	37	((L04-C07 and L04-C12).cpi.) and soi	DERWENT	2004/08/10 19:12
-	17	"5780900"	USPAT	2004/08/11 12:30
-	14	"5097314"	USPAT	2004/08/11 13:54
-	22	(silicon$1on$1insulator soi) and ((high adj voltage) near (area region section portion)) and ((low adj voltage) near (area region section portion))	USPAT	2004/08/11 14:07